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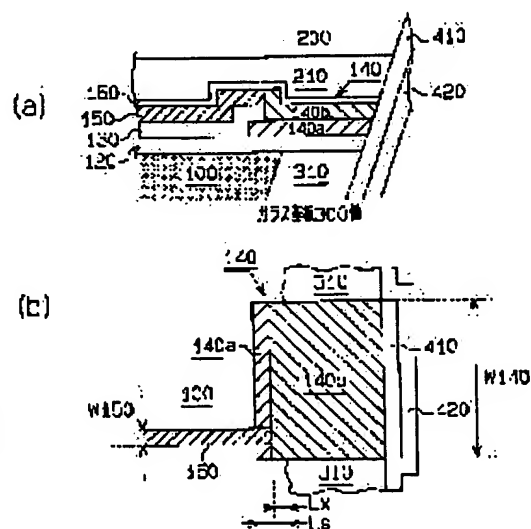
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(54) SEMICONDUCTOR INTEGRATED DEVICE AND ITS MANUFACTURING METHOD

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a semiconductor integrated device wherein concentration of stress which is generated on a wiring in the semiconductor integrated device is relieved and electrical reliability of the device can be maintained to be high, and to provide a method for manufacturing the device.

SOLUTION: A silicon oxide film 120 is formed on a semiconductor chip 100 on which a CCD image sensor is formed and on an epoxy resin 310 by which the semiconductor chip 100 is stuck to a glass substrate which is not shown in figure. An internal pad 140 which makes contact between an external terminal and the CCD image sensor formed on the semiconductor chip 100 is formed on the silicon oxide film 120 via an external wiring 410. An internal wiring 150 whose line width is smaller than electrode width of the internal pad 140 is connected with the internal pad 140, which is formed so as to protrude above the semiconductor chip 100.



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